

Title (en)

LOW TEMPERATURE DEPOSITION OF SILICON OXIDE FILMS

Title (de)

AUFBRINGUNG VON SILICIUMOXIDFILMEN BEI NIEDRIGEN TEMPERATUREN

Title (fr)

DÉPÔT À BASSE TEMPÉRATURE DE FILMS D'OXYDE DE SILICIUM

Publication

EP 2697826 A4 20141022 (EN)

Application

EP 12770650 A 20120329

Priority

- US 201161474415 P 20110412
- US 2012031122 W 20120329

Abstract (en)

[origin: WO2012141908A1] Deposition of silicon oxide films at low temperature by using wet chemistry techniques. The wet chemistry solution may be a mixture of sodium hypochloride (NaOCl), tetra methyl ammonium hydroxide (TMAH) and hydrated silicate, such as silicic acid. The resulting silicon oxide films provide excellent anti-reflective coatings for solar cells and the like.

IPC 8 full level

H01L 31/18 (2006.01); **H01L 21/316** (2006.01); **H01L 31/0216** (2014.01)

CPC (source: EP)

H01L 21/02238 (2013.01); **H01L 31/02168** (2013.01); **H01L 31/18** (2013.01); **Y02E 10/50** (2013.01)

Citation (search report)

- [XAI] US 5616233 A 19970401 - JENN-GWO HWU [TW], et al
- [XAI] US 2002106865 A1 20020808 - CHEN TAI-JU [TW], et al
- [A] EP 1293488 A1 20030319 - TOYO GOSEI KOGYO KK [JP]
- See references of WO 2012141908A1

Designated contracting state (EPC)

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WO 2012141908 A1 20121018; **WO 2012141908 A8 20121122**; EP 2697826 A1 20140219; EP 2697826 A4 20141022; SG 194085 A1 20131129; TW 201307610 A 20130216

DOCDB simple family (application)

US 2012031122 W 20120329; EP 12770650 A 20120329; SG 2013074265 A 20120329; TW 101113065 A 20120412